



HY62C87

65,536×1-Bit CMOS Static RAM

AUGUST 1986

990619

DESCRIPTION

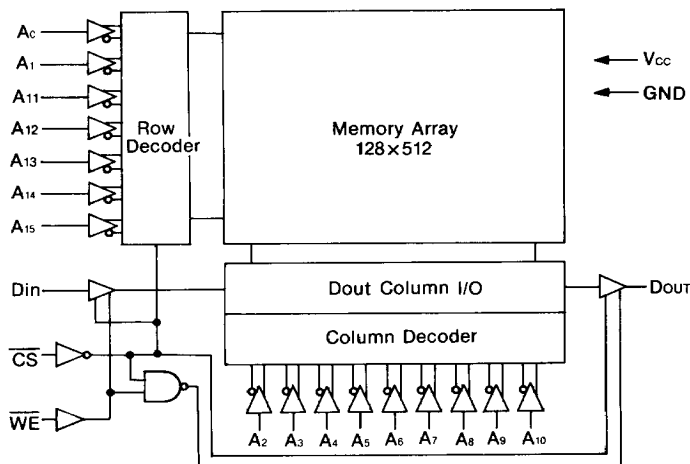
The HY62C87 is a high speed, low power, 65,536×1 bit static CMOS RAM fabricated using high-performance HYCMOS process technology. This high reliability process coupled with innovative circuit design techniques, yields access times of 35 ns. maximum.

When the chip select is brought high, the device assumes a standby mode in which the device power dissipation is reduced to 100 μ W (typically). The HY62C87 has a data retention mode that guarantees data will remain valid at a minimum power supply voltage of 2.0 volts.

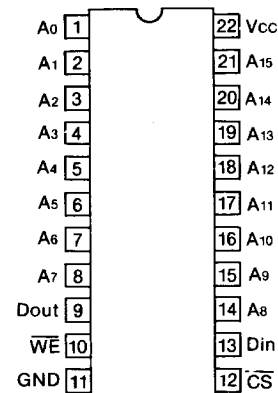
FEATURES

- ▲ 64K×1 High Speed CMOS SRAM
- ▲ High Speed
Access Time 35/45/55 ns
- ▲ Low Power Dissipation
100 μ W (Typ) Standby
250 μ W (Typ) Operating
- ▲ Single 5V±10% Power Supply
- ▲ Battery Back-Up Operation
2.0 – 2.5V Data Retention
- ▲ All Inputs and Outputs Directly TTL Compatible
- ▲ Plastic 300 MIL 22 Pin DIP Package

BLOCK DIAGRAM



PIN CONNECTIONS



(TOP VIEW)



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